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LIST OF DOCUMENTS CITED BY APPLICANT
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Applicants: Das et al.

Filing Date: October 26, 2001

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U. S. PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
7	5,170,231	12/8/92	Fujii et al.	357	23.2	
7	5,972,801	10/26/99	Lipkin et al.	438	770	
7	6,165,822	12/26/00	Okuno et al.	438	142	
7	6,221,700	4/24/01	Okuno et al.	438	151	
7	6,455,892	9/24/02	Okuno et al.	257	328	
7	2002/0072247A1	6/13/02	Lipkin et al.	438	767	

FOREIGN PATENT DOCUMENTS

	Document Number	Date	Country	Class	Subclass	Translation
7	JP02000252461A	9/14/00	Japan	—	—	Abstract

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

7	8	Copy of International Search Report for PCT/US02/11691.	✓
7	9	Xu et al. "Improved Performance and Reliability of N ₂ O-Grown Oxynitride on 6H-SiH," <i>IEEE Electron Device Letters</i> . Vol. 21, No.6, June 2000, p. 298-300.	✓
7	10	Wang et al. "High Temperature Characteristics of High-Quality SiC MIS Capacitors with O/N/O Gate Dielectric," <i>IEEE Transactions on Electron Devices</i> . Vol. 47, No. 2, February 2000, pp. 458-462.	✓
7	11	Lai et al. "Interface Properties of N ₂ O-Annealed NH ₃ -Treated 6H-SiC MOS Capacitor," <i>Electron Devices Meeting</i> , June 26, 1999, pp. 46-9.	✓
7	12	Lipkin et al. "Challenges and State-of-the-Art of Oxides on SiC," <i>Mat. Res. Symp. Proc.</i> Vol. 640, 2001.	✓
7	13	Cho et al. "Improvement of charge trapping by hydrogen post-oxidation annealing in gate oxide of 4H-SiC methel-oxide-semiconductor capacitors," <i>Applied Physics Letters</i> . Vol. 77, No. 8, pp. 1215-7, 8/2 2000	✓
7	14	Fukuda et al. "Improvement of SiO ₂ /4H-SiC Interface Using High-Temperature Hydrogen Annealing at Low Pressure and Vacuum Annealing," <i>Jpn J. Appl. Phys.</i> Vol. 38, April 1999, pp. 2306-9	✓
7	15	Suzuki et al. "Effect of Post-oxidation-annealing in Hydrogen on SiO ₂ /4H-SiC Interface," <i>Materials Science Forum</i> , Vols. 338-342 (2000) 1073-6.	✓
7	16	Leonhard et al. "Long term stability of gate-oxides on n- and p-type silicon carbide studied by charge injection techniques," <i>Materials Science Engineering</i> , Vol. 46, No. 1-3, April 1997, pp. 263-6.	✓
7	17	Fukuda et al. "Improvement of SiO ₂ /4H-SiC Interface by Using High Temperature Hydrogen Annealing at 1000° C," <i>Extended Abstracts of the International Conference on Solid State Devices and Materials</i> , Japan Society of Applied Physics, Tokyo, Japan, Sept. 1998.	✓
7	18	Chang et al. "Observation of a Non-stoichiometric Layer at the Silicon Dioxide--Silicon Carbide Interface: Effect of Oxidation Temperature and Post-Oxidation Processing Conditions," <i>Mat. Res. Soc. Symp. Proc.</i> Vol. 640, 2001.	✓

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